

# PTVA082407NF

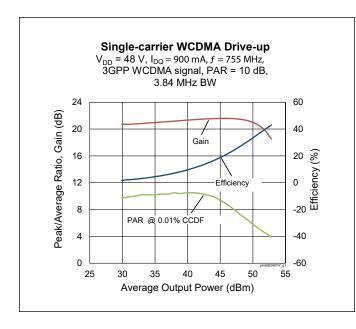
Thermally-Enhanced High Power RF LDMOS FET 240 W, 48 V, 746 - 821 MHz

#### **Description**

The PTVA082407NF is a 240-watt LDMOS FET manufactured with the 48-V LDMOS process. It is designed for use in multi-standard cellular power amplifier applications. It features a single ended design and input matching that allow for use from 746 MHz to 821 MHz. Manufactured with an advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



Package Types: PG-HBSOF-4-2



### **Features**

- Broadband internal input matching
- Typical CW performance, 755 MHz, 48 V
  - Output power at P<sub>1dB</sub> = 225 W
    Output power at P<sub>3dB</sub> = 250 W

  - Gain = 20.5 dB
  - Efficiency = 43%
- Capable of handling 10:1 VSWR @ 48 V, 80 W CW output power
- Integrated ESD protection
- Human Body Model class 2 (per ANSI/ESDA/ JEDEC JS-001)
- Low thermal resistance
- Pb-free and RoHS compliant

#### **RF Characteristics**

**Single-carrier WCDMA Specifications** (tested in the production test fixture)

 $V_{\rm DD}$  = 48 V,  $I_{\rm DQ}$  = 900 mA,  $P_{\rm OUT}$  = 80 W avg, f = 755 MHz, 3GPP signal, channel bandwidth = 3.84 MHz, peak/average = 10 dB @ 0.01% CCDF

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Linear Gain	G <sub>ps</sub>	21	22.5	_	dB
Drain Efficiency	$\eta_{\scriptscriptstyle D}$	33	35.5	_	%
Adjacent Channel Power Ratio	ACPR	_	-31.5	-29.5	dBc

All published data at  $T_{CASE} = 25^{\circ}C$  unless otherwise indicated ESD: Electrostatic discharge sensitive device—observe handling precautions!





#### **DC Characteristics**

Characteristic	Symbol	Min.	Тур.	Max.	Unit	Conditions
Drain-Source Breakdown Voltage	V <sub>BR(DSS)</sub>	105	_	_	V	$V_{GS} = 0 \text{ V}, I_{DS} = 10 \text{ mA}$
Dunin Lookson Current		_	_	1	μΑ	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}$
Drain Leakage Current	DSS	_	_	10		V <sub>DS</sub> = 105 V, V <sub>GS</sub> = 0 V
Gate Leakage Current	I <sub>GSS</sub>	_	_	1		V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0 V
On-State Resistance	R <sub>DS(on)</sub>	_	0.16	_	Ω	$V_{GS} = 10 \text{ V}, V_{DS} = 0.1 \text{ V}$
Operating Gate Voltage	V <sub>GS</sub>	3.3	3.7	4	V	$V_{DS} = 48 \text{ V}, I_{DQ} = 0.9 \text{ A}$

# **Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source Voltage	V <sub>DSS</sub>	105	
Gate-source Voltage	V <sub>GS</sub>	-6 to +12	V
Operating Voltage	V <sub>DD</sub>	0 to +55	
Junction Temperature	T <sub>J</sub>	225	0.0
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C

<sup>1.</sup> Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range (V<sub>DD</sub>) specified above.

#### **Thermal Characteristics**

Parameter	Symbol	Value	Unit	Conditions
Thermal Resistance	$R_{ heta JC}$	0.32	°C/W	T <sub>CASE</sub> = 70°C, 240 W CW

# **Moisture Sensitivity Level**

Level	Test Signal	Package Temperature	Unit
3	IPC/JEDEC J-STD-020	260	°C

#### **Ordering Information**

Type and Version	Order Code	Package Description	Shipping
PTVA082407NF V2 R5	PTVA082407NF-V2-R5	PG-HBSOF-4-2	Tape & Reel, 500 pcs

<sup>2.</sup> Parameters values can be affected by end application and product usage. Values may change over time.

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#### **Typical RF Performance** (data taken in production test fixture)

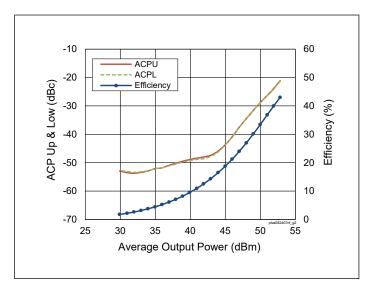


Figure 1. Single-carrier WCDMA Drive-up

 $V_{DD}$  = 48 V,  $I_{DQ}$  = 900 mA, f = 755 MHz, 3GPP WCDMA signal, PAR = 10 dB, BW = 3.84 MHz

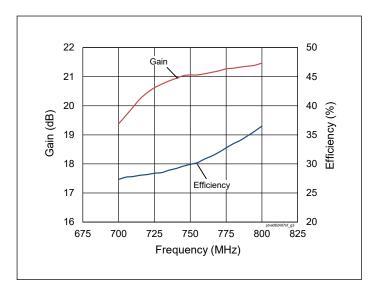


Figure 2. Single-carrier WCDMA Broadband Performance

 $V_{DD}$  = 48 V,  $I_{DQ}$  = 900 mA,  $P_{OUT}$  = 49.03 dBm, 3GPP WCDMA signal, PAR = 10 dB

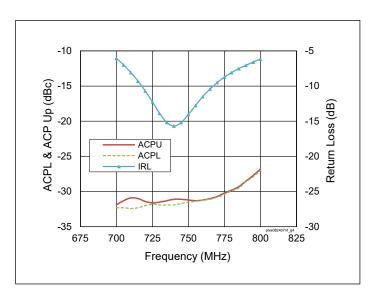


Figure 3. Single-carrier WCDMA Broadband Performance

 $V_{DD}$  = 48 V,  $I_{DQ}$  = 900 mA,  $P_{OUT}$  = 49.03 dBm, 3GPP WCDMA signal, PAR = 10 dB

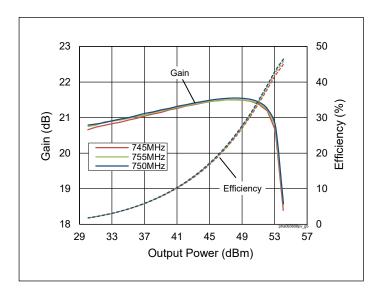
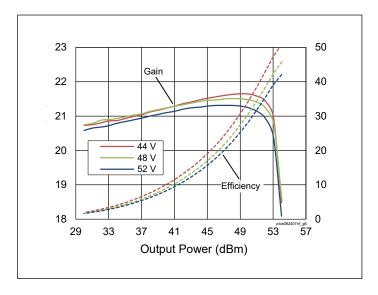


Figure 4. CW Performance

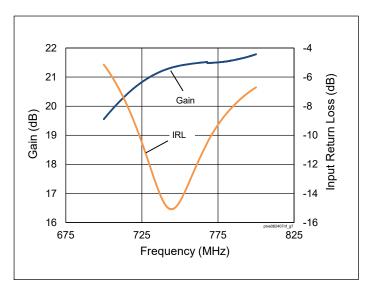
 $V_{\rm DD}$  = 48 V,  $I_{\rm DQ}$  = 900 mA



## **Typical Performance (cont.)**



**Figure 5.** CW Performance at various  $V_{DD}$  $I_{DQ} = 900 \text{ mA}, f = 755 \text{ MHz}$ 



**Figure 6.** CW Performance Small Signal Gain & Input Return Loss

$$V_{DD} = 48 \text{ V}, I_{DQ} = 900 \text{ mA}$$

#### **Load Pull Performance**

**Load Pull Performance –** Pulsed CW signal: 10  $\mu$ s, 10% duty cycle, 48 V, I $_{DO}$  = 500 mA

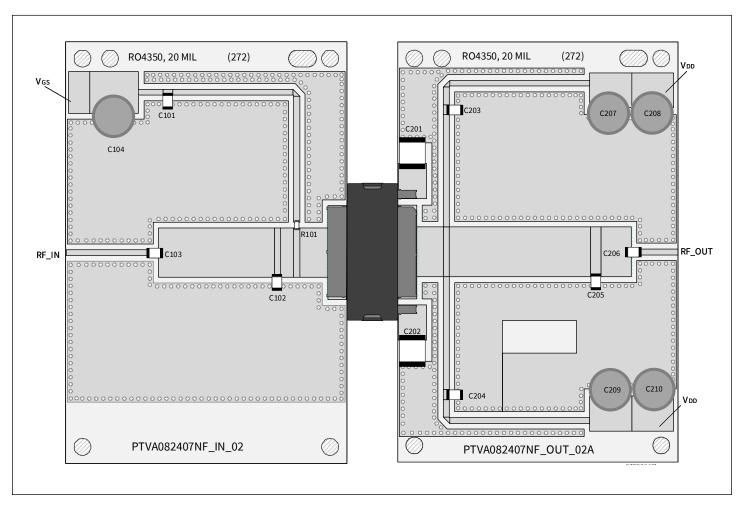
			P <sub>1dB</sub>								
			Max (	Output Po	wer			Max Dr	rain Efficie	ency	
Freq [MHz]	Zs [Ω]	Zl [Ω]	Gain [dB]	P <sub>1dB</sub> [dBm]	P <sub>1dB</sub> [W]	ηD [%]	Zl [Ω]	Gain [dB]	P <sub>1dB</sub> [dBm]	P <sub>1dB</sub> [W]	ηD [%]
740	0.76 – j2.72	1.85 – j0	21.29	55.11	324.3	61.1	3.12 + j1.74	23.18	53.18	208.0	71.0
760	1.03 – j2.98	1.6 – j0	21.26	55.38	345.1	59.5	2.67 + j1.87	23.42	53.05	201.8	71.2
820	3.27 – j2.56	1.63 – j0.26	21.95	54.76	299.2	57.0	2.42 + j1.49	24.13	52.91	195.4	68.6

			P <sub>3dB</sub>								
			Max (	Output Po	wer			Max Dı	ain Efficie	ency	
Freq [MHz]	Zs [Ω]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]
740	0.76 – j2.72	1.83 – j0.45	19.09	55.73	374.1	60.3	2.81 + j1.11	20.82	54.47	279.9	71.7
760	1.03 – j2.98	1.64 – j0.06	19.29	55.98	396.3	61.4	2.49 + j1.36	21.10	54.20	263.0	71.5
820	3.27 – j2.56	1.65 – j0.41	19.85	55.49	354.0	58.6	2.36 + j1.16	21.91	53.94	247.7	69.2

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## Evaluation Board, 746 - 821 MHz



Reference circuit assembly diagram (not to scale)

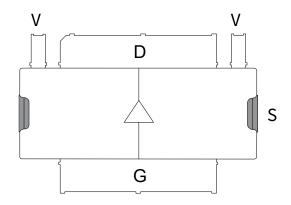
Evaluation Board Part Number	LTN/PTVA082407NF-V2
PCB Information	Rogers 4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\varepsilon_r = 3.66$ , $f = 746 - 821$ MHz



# **Components Information**

Component	Description	Manufacturer	P/N
Input			
C101, C103	Capacitor, 56 pF	ATC	ATC100B560KW500XT
C102	Capacitor, 10 pF	ATC	ATC100B100KW500XT
C104	Capacitor, 100 μF, 50 V	United Chemi-Con	EMVA500ADA101MHA0G
R101	Resistor, 10 ohms	Panasonic Electronic Components	ERJ-8GEYJ100V
Output			
C201, C202	Capacitor, 100 μF, 100 V	TDK Corporation	C5750X7S2A106M230KB
C203, C204, C206	Capacitor, 56 pF	ATC	ATC100B560KW500XT
C205	Capacitor, 6.8 pF	ATC	ATC100B6R8CW500XB
C207, C208, C209, C210	Capacitor, 100 μF, 63 V	Panasonic Electronic Components	EEE-FK1J101P

# Pinout Diagram (top view)



Pin	Description
D	Drain
G	Gate
S	Source (flange)
V	Drain video decoupling (use only
	for decoupling), not for DC bias



#### Package Outline Specifications - Package PG-HBSOF-4-2

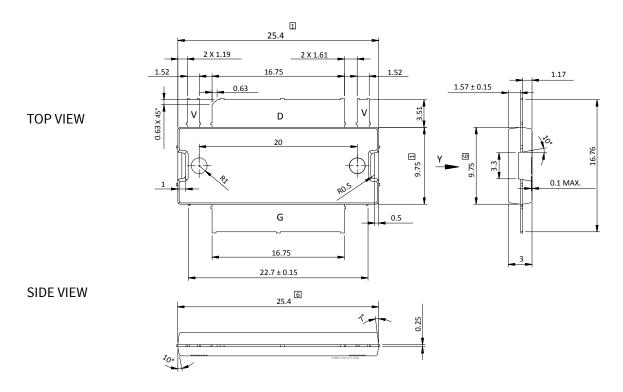
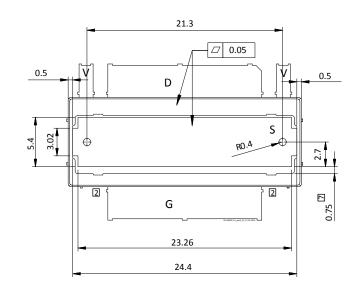


Diagram Notes-unless otherwise specified:

- 1. Mold/dam bar/metal protrusion of 0.30 mm max per side not included.
- 2. Metal protrusion are connected to source and shall not exceed 0.10 mm max.
- 3. Fillets and radii: all radii are 0.3 mm max.
- 4. Interpret dimensions and tolerances per ISO 8015.
- 5. Dimensions are mm.
- 6. Does not include mold/dam bar/metal protrusion.
- 7. Exposed metal surface tin-plated, may not be covered by mold compound.
- 8. All tolerances ± 0.1 mm unless specified otherwise.
- 9. All metal surfaces are tin-plated, except area of cut.
- 10. Lead thickness: 0.25 mm.
- 11. Pins: D drain; G gate; S source; V drain video decoupling (use only for decoupling), not for DC bias



## Package Outline Specifications - Package PG-HBSOF-4-2



BOTTOM VIEW

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